

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

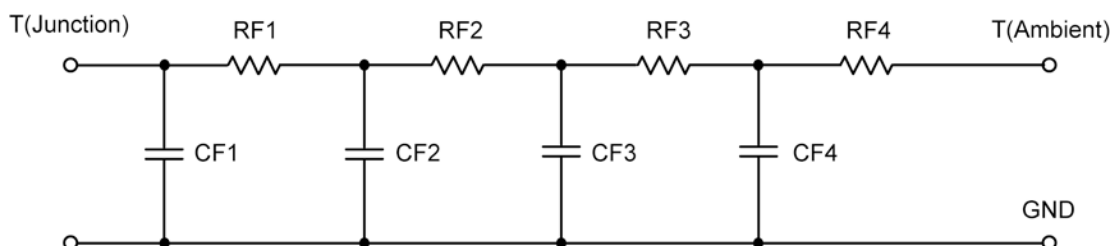
For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|------------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 4.3781 | 886.3418 m | N/A |
| RT2 | 33.9005 | 189.9780 m | N/A |
| RT3 | 11.8113 | 150.1802 m | N/A |
| RT4 | 14.9101 | 1.3735 | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 10.6403 m | 3.6687 m | N/A |
| CT2 | 3.1400 | 1.7116 m | N/A |
| CT3 | 104.5502 m | 424.2065 m | N/A |
| CT4 | 1.5087 | 14.2082 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

| Thermal Resistance (°C/W) | | | |
|---------------------------------|------------|------------|------|
| Junction to | Ambient | Case | Foot |
| RF1 | 4.3670 | 727.7822 m | N/A |
| RF2 | 11.5077 | 710.4071 m | N/A |
| RF3 | 17.8002 | 712.8188 m | N/A |
| RF4 | 31.3251 | 448.9919 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 8.3305 m | 1.1888 m | N/A |
| CF2 | 63.8877 m | 4.9209 m | N/A |
| CF3 | 585.9560 m | 381.4855 u | N/A |
| CF4 | 2.1682 | 55.0827 m | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

